



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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**MMPQ6502**

**SURFACE MOUNT  
COMPLEMENTARY  
SILICON QUAD TRANSISTORS**



[www.centrasemi.com](http://www.centrasemi.com)

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR MMPQ6502, consisting of two complementary pairs of transistors, available in the SOIC-16 surface mount package, is designed for general purpose amplifier and switching applications.

**MARKING: FULL PART NUMBER**

**MAXIMUM RATINGS:** ( $T_A=25^{\circ}\text{C}$ )

	<b>SYMBOL</b>		<b>UNITS</b>
Collector-Base Voltage	$V_{CBO}$	60	V
Collector-Emitter Voltage	$V_{CEO}$	30	V
Emitter-Base Voltage	$V_{EBO}$	5.0	V
Continuous Collector Current	$I_C$	1.0	A
Power Dissipation	$P_D$	1.0	W
Operating and Storage Junction Temperature	$T_J, T_{stg}$	-55 to +150	$^{\circ}\text{C}$
Thermal Resistance (Total Package)	$\theta_{JA}$	125	$^{\circ}\text{C/W}$
Thermal Resistance (Each Transistor)	$\theta_{JA}$	240	$^{\circ}\text{C/W}$

**ELECTRICAL CHARACTERISTICS:** ( $T_C=25^{\circ}\text{C}$  unless otherwise noted)

<b>SYMBOL</b>	<b>TEST CONDITIONS</b>	<b>MIN</b>	<b>MAX</b>	<b>UNITS</b>
$I_{CBO}$	$V_{CB}=50\text{V}$		30	nA
$I_{EBO}$	$V_{BE}=3.0\text{V}$		30	nA
$BV_{CBO}$	$I_C=10\mu\text{A}$	60		V
$BV_{CEO}$	$I_C=10\text{mA}$	30		V
$BV_{EBO}$	$I_E=10\mu\text{A}$	5.0		V
$V_{CE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$		0.4	V
$V_{CE(SAT)}$	$I_C=300\text{mA}, I_B=30\text{mA}$		1.4	V
$V_{BE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$		1.3	V
$V_{BE(SAT)}$	$I_C=300\text{mA}, I_B=30\text{mA}$		2.0	V
$h_{FE}$	$V_{CE}=10\text{V}, I_C=1.0\text{mA}$	50		
$h_{FE}$	$V_{CE}=10\text{V}, I_C=10\text{mA}$	75		
$h_{FE}$	$V_{CE}=10\text{V}, I_C=150\text{mA}$	100		
$h_{FE}$	$V_{CE}=10\text{V}, I_C=300\text{mA}$	30		
$f_T$	$V_{CE}=20\text{V}, I_C=50\text{mA}, f=100\text{MHz}$	200		MHz
$C_{ib}$	$V_{BE}=2.0\text{V}, f=1.0\text{MHz}$		30	pF
$C_{ob}$	$V_{CB}=10\text{V}, f=1.0\text{MHz}$		8.0	pF

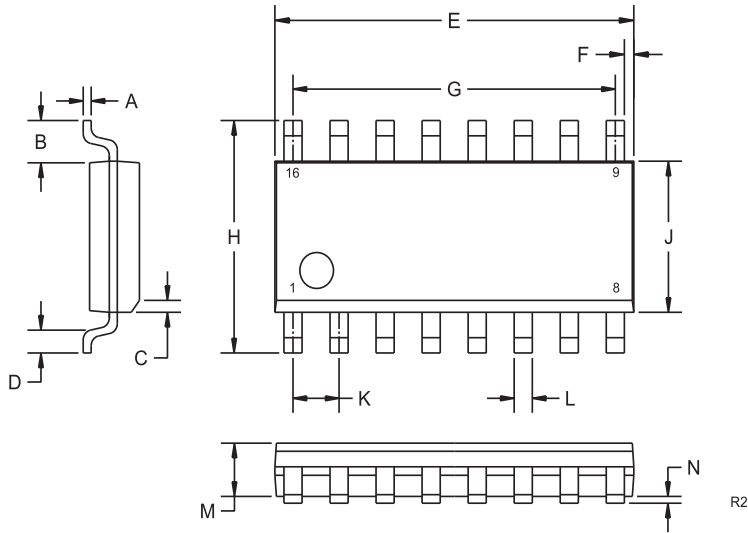
R2 (1-March 2010)

**MMPQ6502**

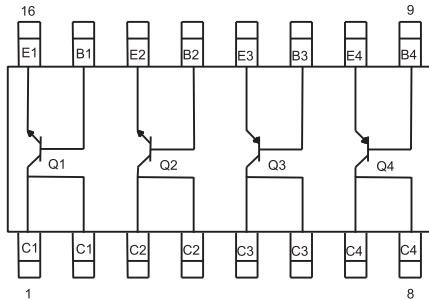
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**SOIC-16 CASE - MECHANICAL OUTLINE**



**PIN CONFIGURATION**



**MARKING: FULL PART NUMBER**

<b>DIMENSIONS</b>				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.007	0.010	0.19	0.25
B	0.041		1.04	
C	0.010	0.020	0.25	0.50
D	0.020	0.035	0.50	0.90
E	0.386	0.394	9.80	10.00
F	0.010		0.25	
G	0.350		8.89	
H	0.228	0.244	5.80	6.20
J	0.150	0.157	3.80	4.00
K	0.050		1.27	
L	0.0138	0.0201	0.35	0.51
M	0.0531	0.0689	1.35	1.75
N	0.0039	0.0098	0.10	0.25

SOIC-16 (REV:R2)

R2 (1-March 2010)